# **ON Semiconductor**

## Is Now



To learn more about onsemi™, please visit our website at www.onsemi.com

onsemi and ONSEMI. and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/ or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use onsemi products for any such unintended or unauthorized application,

# High-Power PNP Silicon Transistor

This transistor is for use as an output device in complementary audio amplifiers to 100–Watts music power per channel.

#### **Features**

- High DC Current Gain  $h_{FE} = 25-100$  @  $I_C = 7.5$  A
- Excellent Safe Operating Area
- Complement to the NPN MJ802
- Pb-Free Package is Available\*

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CER</sub>	100	Vdc
Collector-Base Voltage	V <sub>CB</sub>	100	Vdc
Collector-Emitter Voltage	V <sub>CEO</sub>	90	Vdc
Emitter-Base Voltage	V <sub>EB</sub>	4.0	Vdc
Collector Current	I <sub>C</sub>	30	Adc
Base Current	I <sub>B</sub>	7.5	Adc
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	200 1.14	W W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +200	°C

#### THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$\theta_{\sf JC}$	0.875	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



#### ON Semiconductor®

http://onsemi.com

# 30 AMPERE POWER TRANSISTOR PNP SILICON 100 VOLTS – 200 WATTS



TO-204AA (TO-3) CASE 1-07 STYLE 1

#### **MARKING DIAGRAM**



MJ4502 = Device Code G = Pb-Free Package A = Assembly Location

YY = Year WW = Work Week MEX = Country of Origin

#### ORDERING INFORMATION

Device	Package	Shipping
MJ4502	TO-204	100 Units / Tray
MJ4502G	TO-204 (Pb-Free)	100 Units / Tray

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	•			
Collector–Emitter Breakdown Voltage (Note 1) ( $I_C = 200 \text{ mAdc}, R_{BE} = 100 \Omega$ )	V <sub>(BR)</sub> CER	100	-	Vdc
Collector-Emitter Sustaining Voltage (Note 1) (I <sub>C</sub> = 200 mAdc)	V <sub>CEO(sus)</sub>	90	-	Vdc
Collector–Base Cutoff Current $(V_{CB} = 100 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 100 \text{ Vdc}, I_E = 0, T_C = 150^{\circ}\text{C})$	I <sub>CBO</sub>	- -	1.0 5.0	mAdc
Emitter-Base Cutoff Current $(V_{BE} = 4.0 \text{ Vdc}, I_C = 0)$	I <sub>EBO</sub>	-	1.0	mAdc
ON CHARACTERISTICS				•
DC Current Gain (I <sub>C</sub> = 7.5 Adc, V <sub>CE</sub> = 2.0 Vdc)	h <sub>FE</sub>	25	100	_
Base-Emitter "On" Voltage (I <sub>C</sub> = 7.5 Adc, V <sub>CE</sub> = 2.0 Vdc)	V <sub>BE(on)</sub>	-	1.3	Vdc
Collector–Emitter Saturation Voltage ( $I_C = 7.5$ Adc, $I_B = 0.75$ Adc)	V <sub>CE(sat)</sub>	-	0.8	Vdc
Base–Emitter Saturation Voltage (I <sub>C</sub> = 7.5 Adc, I <sub>B</sub> = 0.75 Adc)	V <sub>BE(sat)</sub>	-	1.3	Vdc
DYNAMIC CHARACTERISTICS		•	•	•
Current Gain – Bandwidth Product (I <sub>C</sub> = 1.0 Adc, V <sub>CE</sub> = 10 Vdc, f = 1.0 MHz)	f <sub>T</sub>	2.0	_	MHz

<sup>1.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

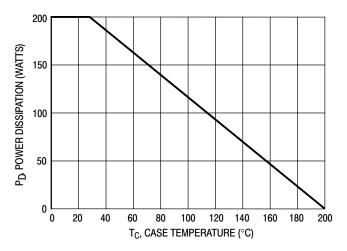


Figure 1. Power-Temperature Derating Curve

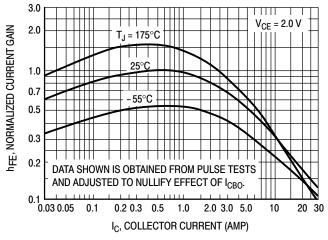


Figure 2. DC Current Gain

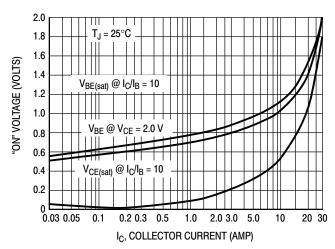


Figure 3. "On" Voltages

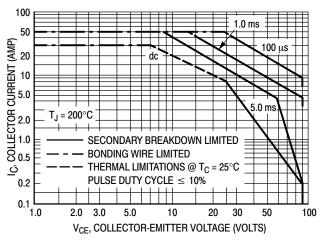
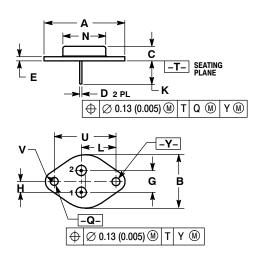


Figure 4. Active Region Safe Operating Area

The Safe Operating Area Curves indicate  $I_C - V_{CE}$  limits below which the device will not enter secondary breakdown. Collector load lines for specific circuits must fall within the applicable Safe Area to avoid causing a catastrophic failure. To insure operation below the maximum  $T_J$ , power–temperature derating must be observed for both steady state and pulse power conditions.

#### PACKAGE DIMENSIONS

**TO-204 (TO-3)** CASE 1-07 ISSUE Z



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
   V14 5M 1982
- Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.
- ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	1.550 REF		39.37 REF	
В		1.050		26.67
С	0.250	0.335	6.35	8.51
D	0.038	0.043	0.97	1.09
E	0.055	0.070	1.40	1.77
G	0.430 BSC		10.92 BSC	
Н	0.215 BSC		5.46 BSC	
K	0.440	0.480	11.18	12.19
L	0.665 BSC		16.89 BSC	
N		0.830		21.08
Q	0.151	0.165	3.84	4.19
U	1.187	BSC	30.15 BSC	
V	0.131	0.188	3.33	4.77

STYLE 1:
PIN 1. BASE
2. EMITTER
CASE: COLLECTOR

ON Semiconductor and IIII are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

#### **PUBLICATION ORDERING INFORMATION**

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81-3-5773-3850 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

# **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below:

619691C MCH4017-TL-H BC546/116 BC557/116 BSW67A NTE158 NTE187A NTE195A NTE2302 NTE2330 NTE63 C4460

2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA2126-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176 FMMTA92QTA

2N2369ADCSM 2SC2412KT146S 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E

US6T6TR 732314D CMXT3906 TR CPH3121-TL-E CPH6021-TL-H 873787E UMX21NTR EMT2T2R MCH6102-TL-E FP204-TL-E

NJL0302DG 2N3583 2SA1434-TB-E 2SC3143-4-TB-E 2SD1621S-TD-E NTE103 30A02MH-TL-E NSV40301MZ4T1G NTE101 NTE13

NTE15 NTE16001